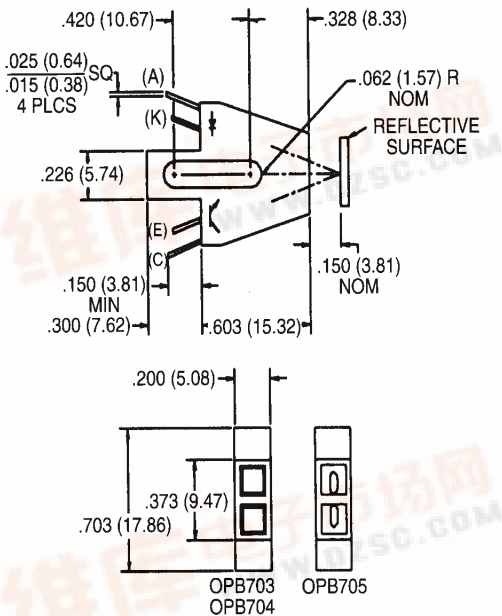




REFLECTIVE OBJECT SENSORS

OPB703/OPB704/OPB705

PACKAGE DIMENSIONS



(C) COLLECTOR
 (E) EMITTER
 (K) CATHODE
 (A) ANODE

ST2154

NOTES:

1. CATHODE AND EMITTER LEADS ARE .050" NOM SHORTER THAN ANODE AND COLLECTOR LEADS.
2. DIMENSIONS ARE IN INCHES (mm).
3. TOLERANCE IS $\pm .010$ (.25) UNLESS OTHERWISE SPECIFIED.

OPB703 - IR TRANSPARENT DUST COVER
 OPB704 - IR TRANSPARENT DUST COVER
 OPB705 - OFFSET LENS

DESCRIPTION

The OPB703, OPB704, and OPB705 consist of an infrared emitting diode and an NPN silicon phototransistor mounted side by side on a converging optical axis in a black plastic housing. The phototransistor responds to radiation from the emitting diode only when a reflective object passes within its field of view. The area of the optimum response approximates a circle .200" in diameter.

FEATURES

- Phototransistor output.
- High Sensitivity.
- Low cost plastic housing.
- OPB703/OPB704, dust cover; lens.
- OPB705, offset lens.



SLOTTED OPTICAL SWITCH

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Specified)	
Storage Temperature	-40°C to $+85^\circ\text{C}$
Operating Temperature	-40°C to $+85^\circ\text{C}$
Soldering:	
Lead Temperature (Iron)	240°C for 5 sec. ^(2,3,4)
Lead Temperature (Flow)	260°C for 10 sec. ^(2,3)
INPUT DIODE	
Continuous Forward Current	50 mA
Reverse Voltage	5.0 Volts
Power Dissipation	100 mW ⁽¹⁾
OUTPUT TRANSISTOR	
Collector-Emitter Voltage	30 Volts
Emitter-Collector Voltage	5.0 Volts
Collector Current	25 mA
Power Dissipation	100 mW ⁽¹⁾

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless Otherwise Specified)					
PARAMETER	SYMBOL	MIN.	MAX.	UNITS	TEST CONDITIONS
INPUT DIODE					
Forward Voltage	V_F	—	1.70	V	$I_F = 40\text{ mA}$
Reverse Leakage Current	I_R	—	100	μA	$V_R = 2.0\text{ V}$
OUTPUT TRANSISTOR					
Emitter-Collector Breakdown	BV_{ECO}	5	—	V	$I_E = 100\ \mu\text{A}$, $E_e = 0$
Collector-Emitter Breakdown	BV_{CEO}	30	—	V	$I_C = 100\ \mu\text{A}$, $E_e = 0$
Collector-Emitter Leakage	I_{CEO}	—	100	nA	$V_{CE} = 10.0\text{ V}$, $E_e = 0$
COUPLED					
On-State Collector Current					
OPB703	$I_{C(ON)}$	200		μA	$I_F = 40\text{ mA}$, $V_{CE} = 5\text{ V}$, $D = .150''$ ^(5,6)
OPB704	$I_{C(ON)}$	200		μA	$I_F = 40\text{ mA}$, $V_{CE} = 5\text{ V}$, $D = .150''$ ^(5,6)
OPB705	$I_{C(ON)}$	100		μA	$I_F = 40\text{ mA}$, $V_{CE} = 5\text{ V}$, $D = .150''$ ^(5,6)
Crosstalk	I_{CX}	—	20	μA	$I_F = 40\text{ mA}$, $V_{CE} = 5\text{V}^{(7)}$

NOTES
1. Derate power dissipation linearly $1.67\text{ mW}/^\circ\text{C}$ above 25°C .
2. RMA flux is recommended.
3. Methanol or Isopropyl alcohols are recommended as cleaning agents.
4. Soldering iron tip $1/16''$ (1.6 mm) from housing.
5. D is the distance from the assembly face to the reflective surface.
6. Measured using Eastman Kodak neutral test card with 90% diffused reflecting surface.
7. Cross talk is the photocurrent measured with current to the input diode and no reflective surface.